



INFORMATION DISCLOSURE STATEMENT

Applicant	:	Skarp et al.
Appl. No.	:	10/003,749
Filed	:	October 23, 2001
For	:	PROCESS FOR PRODUCING ALUMINUM OXIDE FILMS AT LOW TEMPERATURES
Examiner	:	Bret P. Chen
Group Art Unit	:	1762

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

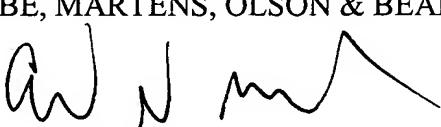
Dear Sir:

Enclosed is form PTO-1449 listing 7 references that are also enclosed. This Information Disclosure Statement is being filed under 37 C.F.R. § 1.97(c)(2) before the mailing date of a final action and before the mailing of a Notice of Allowance. This Statement is accompanied by the fees set forth in 37 C.F.R. § 1.17(p). The Commissioner is hereby authorized to charge any additional fees which may be required or to credit any overpayment to Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: October 22, 2003

By: 
 Andrew N. Merickel
 Registration No. 53,317
 Attorney of Record
 Customer No. 20,995
 (415) 954-4114

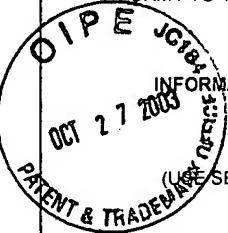
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 FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. SEPP15.001AUS	APPLICATION NO. 10/003,749
	APPLICANT Skarp et al.	
	FILING DATE October 23, 2001	GROUP 1762

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
1	US 2003/0129298 A1	07/10/03	Tera et al.				
2	US 2001/0031379 A1	10/18/01	Tera et al.				
3	US 2002/0003403 A1	01/10/02	Ghosh et al.				
4	US 2001/0052752 A1	12/20/01	Ghosh et al.				

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
5	WO 03/008110 A1	01/30/03	PCT				

* EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
6	Kukli et al, "Atomic layer epitaxy growth of aluminum oxide thin films from a novel Al(CH ₃) ₂ Cl precursor and H ₂ O.", J. Vac. Sci. Technol. A 15(4), July/Aug 1997, pp. 2214-2218	
7	Hiltunen et al. "Growth and Characterization of Aluminum Oxide Thin Films Deposited from Various Source Materials by Atomic Layer Epitaxy and Chemical Vapor Deposition Processes", Materials Chemistry and Physics, 28 (1991) pp. 379-388	
8		
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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMITY WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMITY AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	